

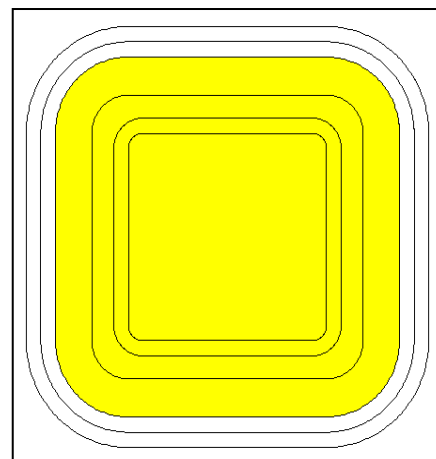
OSZ-1017B-14V SILICON BIDIRECTIONAL ZENER DIODE

ASYMMETRY TYPE BIDIRECTIONAL ZENER DIODE

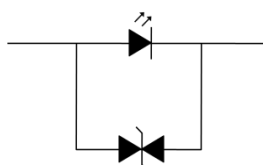
TENTATIVE

APPLICATION : Surge ESD Protector

- DIE SIZE $0.15(\pm 0.02)\text{mm} \times 0.15(\pm 0.02)\text{mm}$
- DIE THICKNESS $100\mu\text{m} \pm 20\mu\text{m}$
- METALLIZATION
 - TOP Au or Al
 - BOTTOM Au
- BONDING PAD SIZE
 - TOP ELECTRODE $0.115\text{mm} \times 0.115\text{mm}$
 - BOTTOM ELECTRODE



• SCHEMATIC DIAGRAM



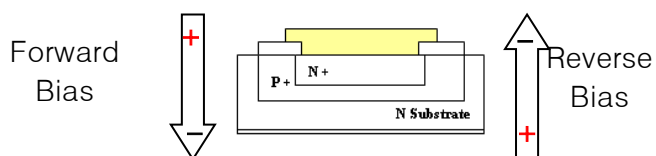
• ANNOTATION :

- Parallel with one LED
- Single pad (one wire bonding applied only)
- Double direction Zener diode protection

• ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Zener Voltage	$V_{Z(R)}$	$I_Z=5\text{mA}$	11.0		19.5	V
Forward Zener Voltage	$V_{Z(F)}$	$I_F=5\text{mA}$	5.0		8.0	V
Reverse Current	I_R	$V_R=10.0\text{V}$			0.1	μA
Forward Current	I_F	$V_F=4.0\text{V}$			0.1	μA

• THE DIRECTION OF BIAS IS USED TO ELECTRICAL CHARACTERISTICS TEST



• ABSOLUT MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Maximum Rating	Unit
Power Dissipation	P_d	30	mW
Junction Temperature	T_J	150	$^\circ\text{C}$

ASYMMETRY TYPE BIDIRECTIONAL ZENER DIODE

PART NAME : BIDIRECTIONAL ZENER DIODE

PART NUMBER : OSZ-1017B-14V

Unit: μm

